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Synthesis and Properties of Regioregular Poly(3-substituted thiophene) Bearing Disiloxane Moiety in the Substituent. Remarkably High Solubility in Hexane

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Regioregular poly(3-substituted thiophene) derivative bearing pentamethyldisiloxane moiety at the 3-substituent is prepared by nickel-catalyzed polymerization reactions with dehydrobrominative or debrominative generation of the organometallic monomer. The monomer precursors 2-bromo-3-(4pentamethyldisiloxybutan-1-yl)thiophene (1a) and 2,5-dibromo-3-(4-pentamethyldisiloxybutan-1-yl)thiophene (1b) are prepared from 3-methylthiophene with 4-5 steps in overall good vields. Treatment of 1a with TMPMgCl·LiCl at room temperature for 3 h forms an organometallic monomer and following the addition of a nickel catalyst affords the corresponding polythiophene bearing a disiloxane moiety in the side chain. The reaction of 1b with Grignard reagent leads to the similar monomer and addition of a catalytic amount of [NiCl₂(dppe)] also affords polythiophene in highly regioregular manners. The obtained polythiophene is found to be dissolved in a hydrocarbon such as hexane.

Synthesis of regioregular poly(3-substituted thiophene)s attracts much attention because of their wide-ranging utilities as materials. It is, therefore, important to develop a new class of high-performance polythiophene derivatives. In particular, considerable attention has been paid to develop flexible and highly processible materials. Siloxane bearing SiOSi linkage with a longer bond distance and a strong bond energy generating flexible but chemically and thermally stable compounds² is a promising structure that may fulfill the above requirements. It is thus intriguing to introduce siloxane moieties into the substituent because it is well known that the polymeric materials bearing a siloxane group generally improve solubility in organic solvents, particularly in hydrocarbons; moreover, such compounds exhibit excellent thermal stability that induces easy fabrication of functionalized polymeric thin films.³ However, there are few examples for the preparation of regionegular poly(3-substituted thiophene) bearing a siloxane moiety in the substituent. Only limited reports of nonregioregular polythiophene that is synthesized by oxidative polymerization with Fe^{III} reagents have been shown with a siloxane-containing 3-substituted thiophene as a monomer species.⁴ On the other hand, regioregular polythiophenes are shown to be synthesized with 2-halo- or 2,5dihalothiophene derivatives as a monomer precursor, which is in situ transformed into the corresponding organometallic thiophene by deprotonation with a metallic amide⁵ or dehalogenative metalation with the Grignard metathesis (GRIM) via halogen-metal exchange.⁶⁻⁸ Nevertheless, a few studies have been reported on the synthesis of halogenated thiophenes bearing a siloxane group,⁴ probably due to the synthetic difficulties in the halogenation of the thiophene ring when a siloxane group exists in the substituent. Herein, we report the preparation of regioregular poly(3-substituted thiophene) bearing a pentamethyldisiloxy group by dehydrogenative or GRIM polymerization with a nickel catalyst, whose success is based on an effective synthetic pathway for the monomer precursor.

Synthesis of the monomer precursor bromothiophenes 1a and 1b was achieved, as represented in Scheme 1. Both compounds were prepared starting from ubiquitous 3-methylthiophene (2) via halogenation of the thiophene ring and following radical bromination to afford 3-(bromomethyl)halothiophenes 4a and 4b. Treatment of 2 with an equimolar amount of N-bromosuccinimide (NBS) leads to 2-bromo-3-methylthiophene (3a), while the reaction with 2 equivalents of NBS furnished 2,5-dibromo-3-methylthiophene (3b). These thiophenes are subjected to radical bromination with NBS in the presence of AIBN in CCl₄, leading to 4a and 4b in 62% and 55% yields, respectively. The reaction of 4a with allylmagnesium chloride afforded 2-bromo-3-(3-buten-1-yl)thiophene (5a), whereas the similar reaction of 4b afforded a side product also allylated at the 5-position along with the desired 5b. Transformation into 5b with an improved yield was achieved by the use of the iodomethyl derivative, which was formed by the treatment of NaI in acetone, to afford 5b. Introduction of

i) NBS, AIBN/CCI₄ ii) NaI (2 equiv)/(CH₃)₂CO iii) H₂C=CHCH₂MgCl/THF

Scheme 1. Preparation of thiophene monomers 1a and 1b bearing a pentamethyldisiloxane moiety.

$$(CH_{2})_{4} - \stackrel{|}{S}i - O - \stackrel{|}$$

Scheme 2. Nickel-catalyzed dehydrobrominative polymerization of 1a with Knochel-Hauser base.

pentamethyldisiloxy group into the obtained **5a** and **5b** was carried out with pentamethyldisiloxane by hydrosilylation with a platinum catalyst leading to **1a** and **1b** in >99% and 93% yields, respectively.

The key for successful preparation of brominated thiophene derivatives bearing a pentamethyldisiloxane moiety is the use of 3-halomethylated thiophene, which allowed treatment of the allyl Grignard reagent to afford 3-(3-buten-1-yl)halothiophenes; otherwise, halogenation of the thiophene ring with NBS would be unsuccessful for the thiophene derivatives bearing a carboncarbon double bond. Furthermore, the disiloxane moiety would not be tolerable toward metalation—bromination with a strong base and following treatment of Br⁺. In contrast, the synthetic pathway shown in Scheme 1 proceeded to afford halothiophenes in reasonable overall yields, thus providing practical synthesis leading to the corresponding polythiophene.

The obtained monomer precursor 1a was then subjected to polymerization by deprotonation with the Knochel–Hauser base⁹ (60 °C, 1 h), following cross-coupling polycondensation with a nickel(II) catalyst.5 Use of the reaction condition that was available for the synthesis of regionegular poly(3-hexylthiophene) was found to be successful in affording the corresponding polythiophene bearing a disiloxane moiety. When 1.0 mol % of [NiCl₂(PPh₃)(IPr)] was employed for the polymerization, polymer 6 was obtained in 93% yield to exhibit $M_{\rm n}$ of 12300 $(M_{\rm w}/M_{\rm n}=1.81)$, as shown in Scheme 2. The HT-regionegularity of 6 was estimated to be >98% by the measurement of ¹H NMR (see Supporting Information). It is remarkable that the color of the reaction mixture remains clear reddish-orange throughout the polymerization. This sharply contrasts with the preparation of regioregular poly(3-hexylthiophene) (HT-P3HT), whose reaction mixture gradually turns to heterogeneous dark purple suspension with the progress of polymerization.^{5–8}

We next examined GRIM polymerization⁸ of 2,5-dibromothiophene derivative bearing siloxane **1b**. Treatment of **1b** with an equimolar amount of *i*-PrMgCl·LiCl to form the corresponding thienyl Grignard reagent and addition of nickel(II) catalyst [NiCl₂(dppe)] (1.0 mol %) induced the polymerization leading to **6** (Scheme 3). The obtained polymer showed M_n of 10500 ($M_w/M_n = 1.13$) and the regioregularity was also found to be excellent (>99:1).

It should be pointed out that the obtained polythiophene bearing a pentamethyldisiloxane moiety $\mathbf{6}$ was found to be soluble in hexanes. When polythiophene $\mathbf{6}$, whose $M_{\rm n}$ and PDI were 12300 and 1.81, respectively, was dissolved in hexane

1b
$$\frac{i - \text{PrMgCl·LiCl}}{1 \text{ equiv}}$$
 [NiCl₂(dppe)] $\frac{1.0 \text{ mol}\%}{60 \text{ °C}, 24 \text{ h}}$ $\frac{6}{59\%}$ $M_{\text{n}} = 10500, \text{PDI} = 1.13$

Scheme 3. Nickel-catalyzed debrominative GRIM polymerization of **1b**.

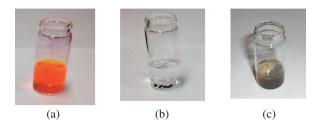
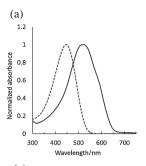
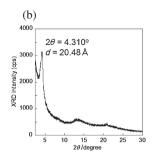


Figure 1. Attempted dissolution of 1 mg of polythiophene derivatives in 1 mL of hexane. (a) Polythiophene **6** bearing siloxane moiety, $M_n = 12300$, PDI = 1.81; (b) poly(3-hexylthiophene), $M_n = 12500$, PDI = 1.35; (c) poly(3-dodecylthiophene), $M_n = 12200$, PDI = 1.72.

 (1 mg mL^{-1}) at room temperature, a clear deep orange solution was immediately formed, as shown in Figure 1a, while other regioregular polythiophene poly(3-hexylthiophene) ($M_n = 12500$, PDI = 1.35) was shown to be hardly soluble under similar conditions, as observed in Figure 1b. Although polythiophene bearing a longer alkyl chain poly(3-dodecylthiophene) ($M_n = 12200$, PDI = 1.72) slightly improved the solubility (Figure 1c), it was found to be much inferior to that of **6**.

The obtained polymer was used to measure spectroscopic and physical properties. Polythiophene 6 was dissolved in hexane and spin coated. The corresponding thin film of 53-nm thickness was obtained after annealing at 110 °C for 10 min. Measurement of UV-vis absorption spectrum exhibited the λ_{max} value of 519 nm in the film. Comparison of the spectra in a hexane solution ($\lambda_{\text{max}} = 446 \,\text{nm}$) and in the film state reveals that the latter has a red-shifted absorption, as shown in Figure 2a, indicating strong interchain interactions among the thiophene chains in the film. The XRD analysis of polythiophene 6 was then performed to observe a peak at $2\theta = 4.310^{\circ}$, suggesting edge-on orientation and a layer distance of d =20.48 Å. Comparing with HT-P3HT ($2\theta = 5.325^{\circ}$, d = 16.60 Å), the layer distance of 6 was found to be slightly longer because of the steric bulkiness of the siloxane moiety (Figure 2b). The HOMO level of the thin-film of 6 bearing siloxane moiety is estimated to be $-4.96\,\mathrm{eV}$ by photoelectron yield spectroscopy, which was found to be slightly lower than that of P3HT $(-4.74 \,\mathrm{eV})$. This is because of better π stacking and improved interchain coupling in the HT-P3HT film that enhances the donor character. This tendency is in accordance with the literature that shorter side chains in regioregular poly(3-substituted thiophene) enhances the donor character.¹⁰ The observation of the AFM image of the thin film of 6 is performed as shown in Figure 2c, indicating a flat film within the region $5 \mu m \times 5 \mu m$, in which the root mean square (RMS) roughness of the film was 1.45 nm. Further studies on the use of the thin film of polythiophene 6





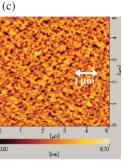


Figure 2. (a) UV–vis spectrum of thin film (solid line), as a hexane solution (dot line); (b) XRD profile; (c) AFM image $(5 \, \mu m \times 5 \, \mu m)$ of **6** (film).

bearing a siloxane moiety in the side chain as electronic devices such as thin-film photovoltaic cells and organic thin-film transistors are under way and will be described in due course.

In conclusion, we have shown the synthesis of regioregular poly(3-substituted thiophene) bearing a siloxane moiety in the substituent. Synthesis of the monomer precursors 1a and 1b was successfully achieved in 5-6 steps with reasonable yields. Polymerization was revealed to proceed via deprotonative or GRIM metalation, and following nickel-catalyzed catalysttransfer polymerization, it afforded polythiophene 6. The obtained polythiophene was found to be dissolved in hexane, while the related alkylthiophenes were hardly soluble. Fabrication of the thin film of 6 was also achieved by spin coating to reveal the HOMO level of -4.96 eV by photoelectron yield spectroscopy and edge-on orientation with a layer distance of 20.48 Å. Utilizing the high solubility of 6 in hydrocarbons, the polymer would allow the environmentally friendly formation of electronic devices as well as improving the solvent choice in the preparation of multilayered thin-film materials.¹¹

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